

Schottky Barrier Diode

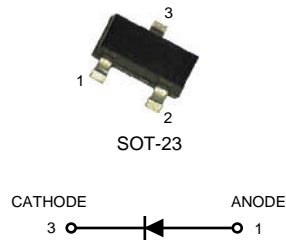
Lead free product

30 VOLTS
SCHOTTKY BARRIER
DETECTOR AND SWITCHING
DIODE

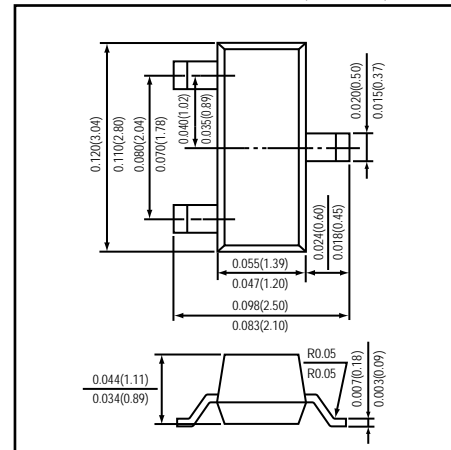
These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- * Extremely Fast Switching Speed
- * Low Forward Voltage-0.35 Volts (Typ) @ $I_F=10\text{mA}$

BAT54RG



*Dimensions in inches and (millimeters)



MAXIMUM RATINGS ($T_J=125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	VR	30	Volts
Forward Power Dissipation @ $T_A=25^\circ\text{C}$ Derate above 25°C	PF	200 2.0	mW mW / $^\circ\text{C}$
Forward Current (DC)	IF	200 Max	mA
Operating Junction Temperature Range	TJ	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	TSTG	-55 to +150	$^\circ\text{C}$

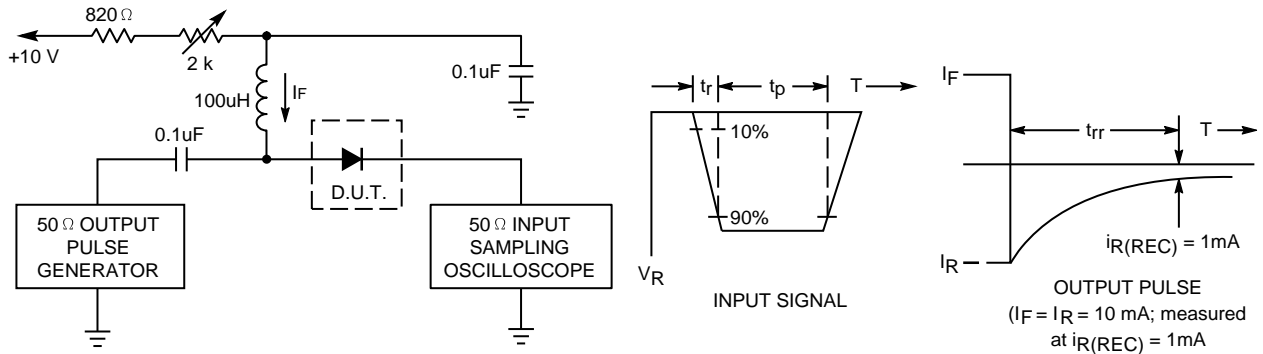
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_R=10\text{ }\mu\text{A}$)	V(BR)	30	-	-	Volts
Forward Voltage ($I_F=0.1\text{ mA}$) ($I_F=1.0\text{ mA}$) ($I_F=10\text{ mA}$) ($I_F=30\text{ mA}$) ($I_F=100\text{ mA}$)	VF	-	0.22 0.29 0.35 0.41 0.52	0.24 0.32 0.40 0.50 1.00	Vdc
Reverse Leakage ($V_R=25\text{ Vdc}$)	IR	-	0.5	2.0	μA
Diode Capacitance ($V_R=1.0\text{V}$, $f=1.0\text{MHz}$)	CJ	-	7.6	10	pF
Reverse Recovery Time ($I_F=I_R=10\text{ mA}$, $I_R(\text{REC})=1.0\text{ mA}$)	trr	-	-	5.0	nS

FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT



- Notes: 1. A 2.0kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10mA.
 3. $t_p \gg t_{rr}$

FIGURE 2. FORWARD VOLTAGE

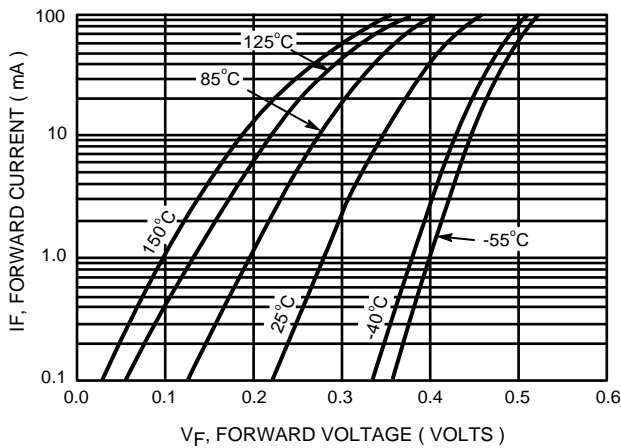


FIGURE 3. LEAKAGE CURRENT

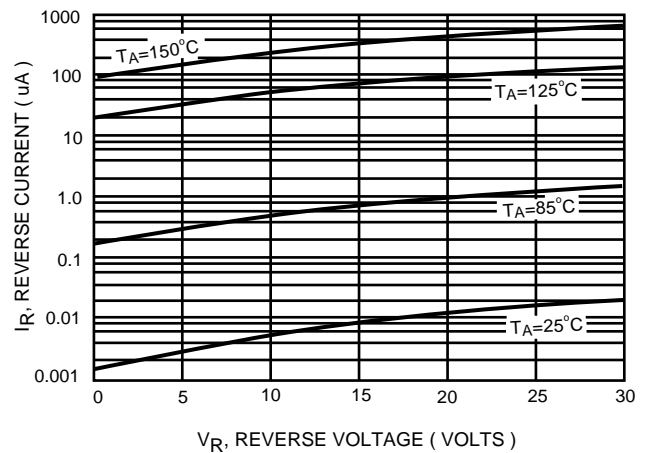


FIGURE 4. TOTAL CAPACITANCE

